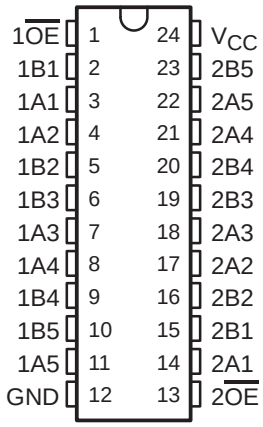
- Output Voltage Translation Tracks V_{CC}
- Supports Mixed-Mode Signal Operation On All Data I/O Ports
  - 5-V Input Down To 3.3-V Output Level Shift With 3.3-V V_{CC}
  - 5-V/3.3-V Input Down To 2.5-V Output Level Shift With 2.5-V V_{CC}
- 5-V-Tolerant I/Os With Device Powered-Up or Powered-Down
- Bidirectional Data Flow, With Near-Zero Propagation Delay
- Low ON-State Resistance (r_{on}) Characteristics (r_{on} = 5 Ω Typical)
- Low Input/Output Capacitance Minimizes Loading ($C_{io(OFF)}$ = 5 pF Typical)
- Data and Control Inputs Provide Undershoot Clamp Diodes
- Low Power Consumption (I_{CC} = 40 μA Max)
- V_{CC} Operating Range From 2.3 V to 3.6 V
- Data I/Os Support 0 to 5-V Signaling Levels (For Example: 0.8-V, 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, 5-V)
- Control Inputs Can Be Driven by TTL or 5-V/3.3-V/2.5-V CMOS Outputs
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- Supports Digital Applications: Level Translation, Memory Interleaving, Bus Isolation
- Ideal for Low-Power Portable Equipment

DBQ, DGV, DW, OR PW PACKAGE
(TOP VIEW)



description/ordering information

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 85°C	SOIC − DW	Tube	SN74CB3T3384DW	CB3T3384
		Tape and reel	SN74CB3T3384DWR	
	SSOP (QSOP) − DBQ	Tape and reel	SN74CB3T3384DBQR	CB3T3384
	TSSOP − PW	Tube	SN74CB3T3384PW	KS384
		Tape and reel	SN74CB3T3384PWR	
	TVSOP − DGV	Tape and reel	SN74CB3T3384DGVR	

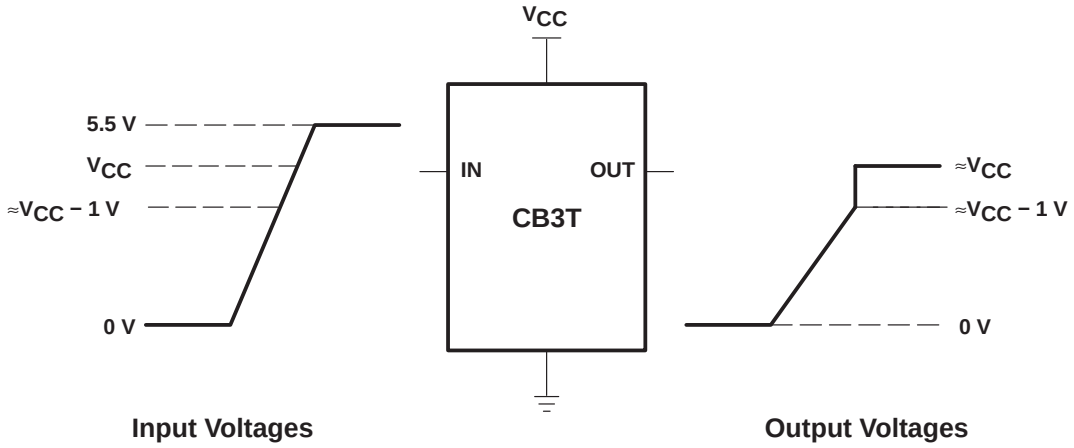
PACKAGE PREVIEW

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

description/ordering information (continued)

The SN74CB3T3384 is a high-speed TTL-compatible FET bus switch with low ON-state resistance (r_{on}), allowing for minimal propagation delay. The device fully supports mixed-mode signal operation on all data I/O ports by providing voltage translation that tracks V_{CC}. The SN74CB3T3384 supports systems using 5-V TTL, 3.3-V LVTTL, and 2.5-V CMOS switching standards, as well as user-defined switching levels (see Figure 1).



NOTE A: If the input high voltage (V_{IH}) level is greater than or equal to V_{CC} − 1 V, and less than or equal to 5.5 V, the output high voltage (V_{OH}) level will be equal to approximately the V_{CC} voltage level.

Figure 1. Typical DC-Voltage-Translation Characteristics

The SN74CB3T3384 is organized as two 5-bit bus switches with separate ouput-enable ($1\overline{OE}$, $2\overline{OE}$) inputs. It can be used as two 5-bit bus switches or as one 10-bit bus switch. When $\overline{OE}$ is low, the associated 5-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When $\overline{OE}$ is high, the associated 5-bit bus switch is OFF, and a high-impedance state exists between the A and B ports.

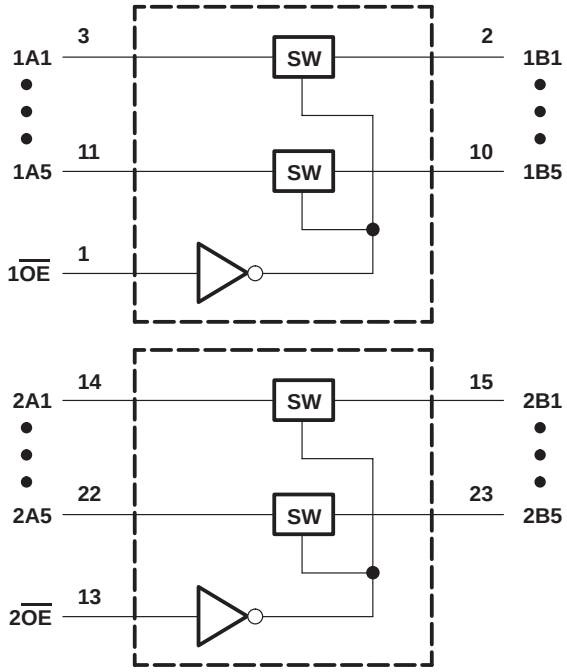
This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The device has isolation during power off.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

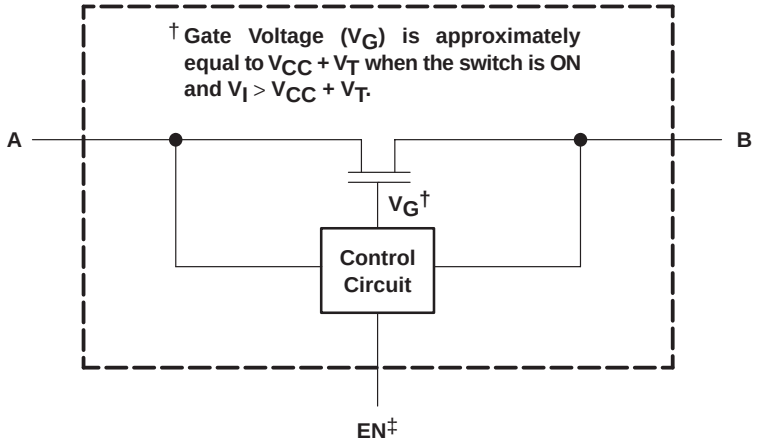
FUNCTION TABLE
(each 5-bit bus switch)

INPUT $\overline{OE}$	INPUT/OUTPUT A	FUNCTION
L	B	A port = B port
H	Z	Disconnect

logic diagram (positive logic)



simplified schematic, each FET switch (SW)



‡ EN is the internal enable signal applied to the switch.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1) . . . . . −0.5 V to 7 V
Control input voltage range, V_{IN} (see Notes 1 and 2) . . . . . −0.5 V to 7 V
Switch I/O voltage range, $V_{I/O}$ (see Notes 1, 2, and 3) . . . . . −0.5 V to 7 V
Control input clamp current, I_{IK} (V_{IN} < 0) . . . . . −50 mA
I/O port clamp current, $I_{I/OK}$ ($V_{I/O}$ < 0) . . . . . −50 mA
ON-state switch current, $I_{I/O}$ (see Note 4) . . . . . ±128 mA
Continuous current through V_{CC} or GND terminals . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 5): DBQ package . . . . . 61°C/W
DGV package . . . . . 86°C/W
DW package . . . . . 46°C/W
PW package . . . . . 88°C/W
Storage temperature range, T_{stg} . . . . . −65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to ground unless otherwise specified.
2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
3. V_I and V_O are used to denote specific conditions for $V_{I/O}$.
4. I_I and I_O are used to denote specific conditions for $I_{I/O}$.
5. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 6)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltage	V_{CC} = 2.3 V to 2.7 V	1.7	5.5	V
		V_{CC} = 2.7 V to 3.6 V	2	5.5	
V_{IL}	Low-level control input voltage	V_{CC} = 2.3 V to 2.7 V	0	0.7	V
		V_{CC} = 2.7 V to 3.6 V	0	0.8	
$V_{I/O}$	Data input/output voltage		0	5.5	V
T_A	Operating free-air temperature		−40	85	°C

NOTE 6: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{IK}		V_{CC} = 3 V, I_I = −18 mA				−1.2	V
V_{OH}		See Figures 3 and 4					
I_{IN}	Control inputs	V_{CC} = 3.6 V, V_{IN} = 3.6 V to 5.5 V or GND				±10	µA
I_I		V_{CC} = 3.6 V, Switch ON, V_{IN} = GND	V_I = V_{CC} − 0.7 V to 5.5 V			±20	µA
			V_I = 0.7 V to V_{CC} − 0.7 V			−40	
			V_I = 0 to 0.7 V			±5	
I_{OZ}‡		V_{CC} = 3.6 V, V_O = 0 to 5.5 V, V_I = 0, Switch OFF, V_{IN} = V_{CC}				±10	µA
I_{off}		V_{CC} = 0, V_O = 0 to 5.5 V, V_I = 0				10	µA
I_{CC}		V_{CC} = 3.6 V, $I_{I/O}$ = 0, Switch ON or OFF, V_{IN} = V_{CC} or GND	V_I = V_{CC} or GND			40	µA
			V_I = 5.5 V			40	
ΔI_{CC}§	Control inputs	V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND				300	µA
C_{in}	Control inputs	V_{CC} = 3.3 V, V_{IN} = V_{CC} or GND			3		pF
$C_{io(OFF)}$		V_{CC} = 3.3 V, $V_{I/O}$ = 5.5 V, 3.3 V, or GND, Switch OFF, V_{IN} = V_{CC}			5		pF
$C_{io(ON)}$		V_{CC} = 3.3 V, Switch ON, V_{IN} = GND	$V_{I/O}$ = 5.5 V or 3.3 V		4		pF
			$V_{I/O}$ = GND		12		
r_{on}¶		V_{CC} = 2.3 V, TYP at V_{CC} = 2.5 V, V_I = 0	I_O = 24 mA		5	8	Ω
			I_O = 16 mA		5	8	
		V_{CC} = 3 V, V_I = 0	I_O = 64 mA		5	7	
			I_O = 32 mA		5	7	

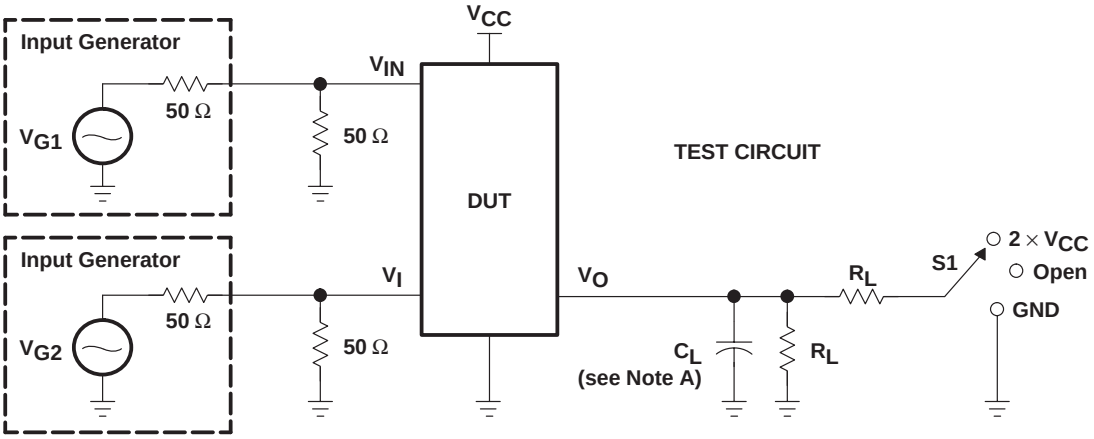
V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
† All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
¶ Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

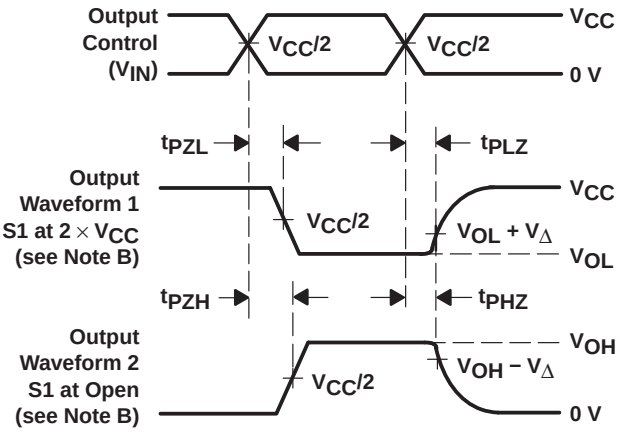
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}†	A or B	B or A		0.15		0.25	ns
t_{en}	$\overline{OE}$	A or B	1	10.5	1	7.5	ns
t_{dis}	$\overline{OE}$	A or B	1	6.5	1	8	ns

† The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

PARAMETER MEASUREMENT INFORMATION



TEST	V_{CC}	S1	R_L	V_I	C_L	V_Δ
t_{PLZ}/t_{PZL}	2.5 V ± 0.2 V	2 × V_{CC}	500 Ω	GND	30 pF	0.15 V
	3.3 V ± 0.3 V	2 × V_{CC}	500 Ω	GND	50 pF	0.3 V
t_{PHZ}/t_{PZH}	2.5 V ± 0.2 V	Open	500 Ω	3.6 V	30 pF	0.15 V
	3.3 V ± 0.3 V	Open	500 Ω	5.5 V	50 pF	0.3 V



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.

Figure 2. Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS

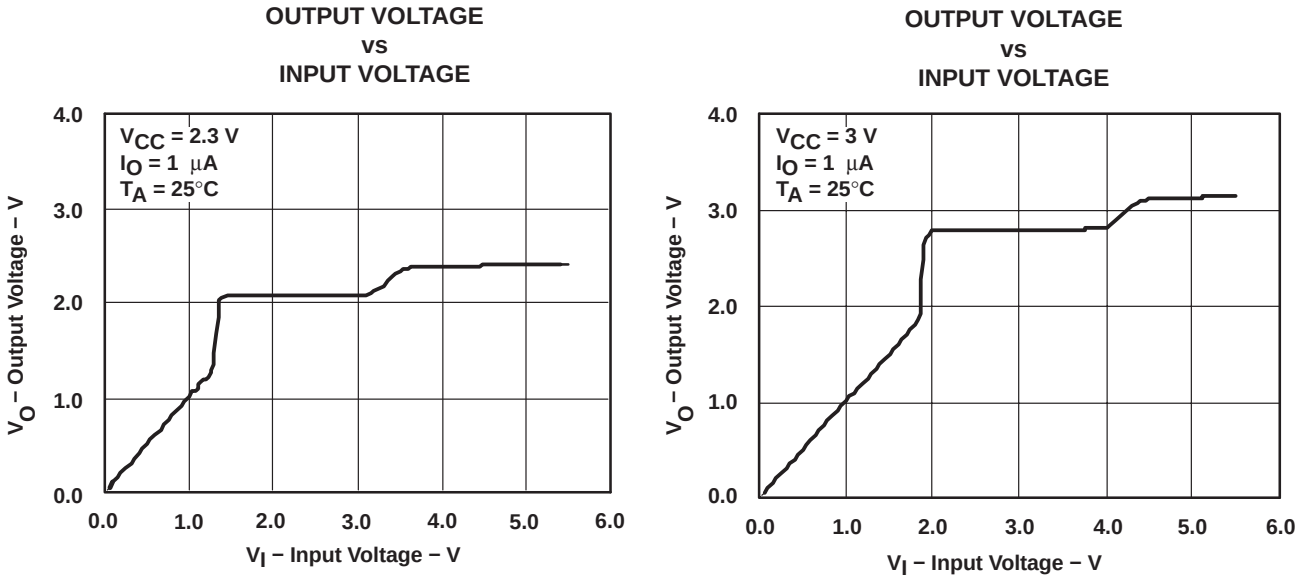
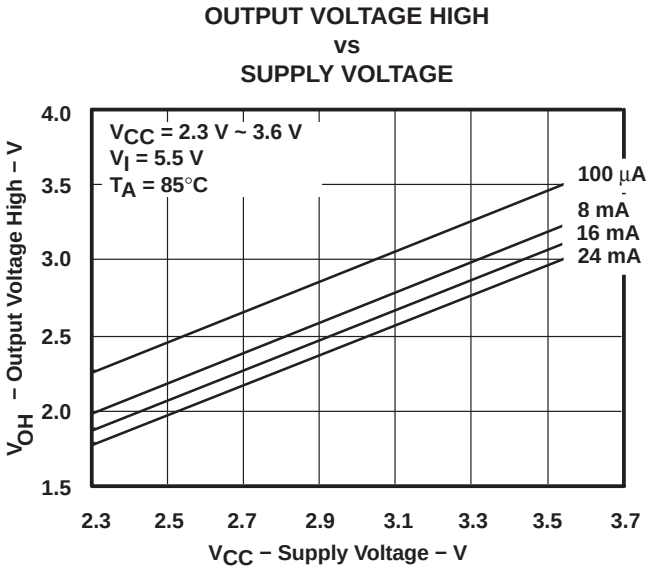
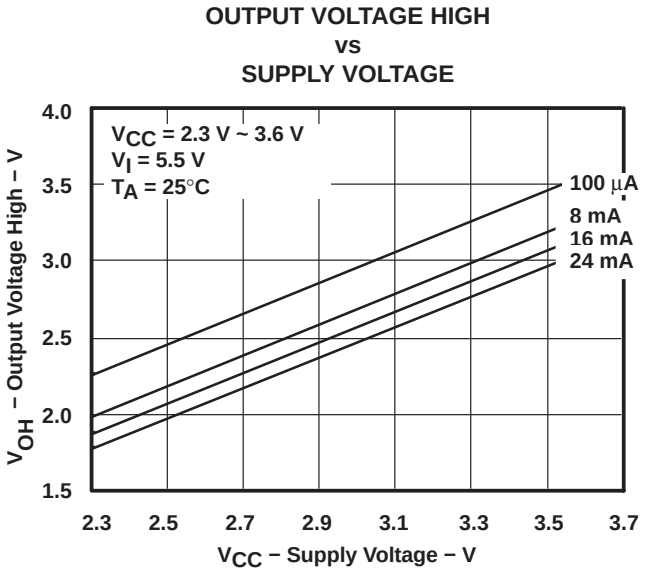


Figure 3. Data Output Voltage vs Data Input Voltage

TYPICAL CHARACTERISTICS (continued)





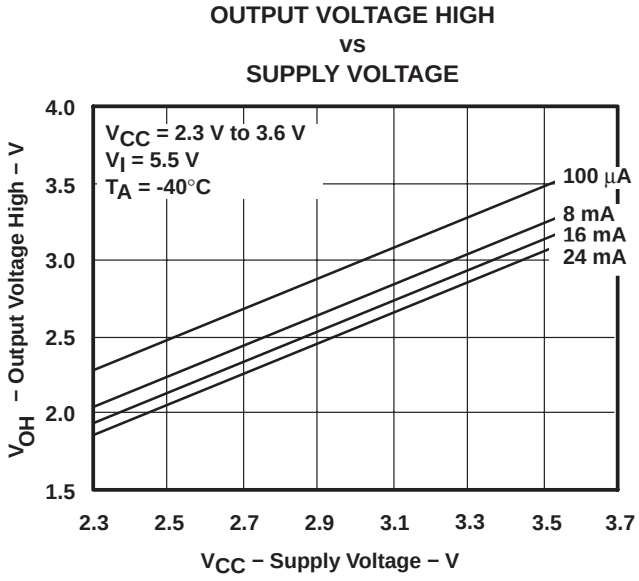


Figure 4. V_{OH} Values

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74CB3T3384DBQR	ACTIVE	SSOP	DBQ	24	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CB3T3384	Samples
SN74CB3T3384DW	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3384	Samples
SN74CB3T3384DWR	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CB3T3384	Samples
SN74CB3T3384PW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS384	Samples
SN74CB3T3384PWG4	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS384	Samples
SN74CB3T3384PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS384	Samples
SN74CB3T3384PWRG4	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS384	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

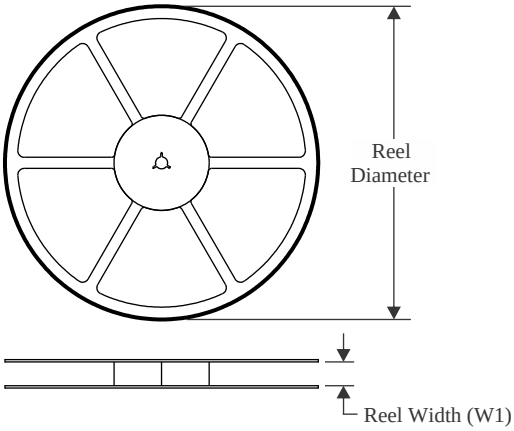
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

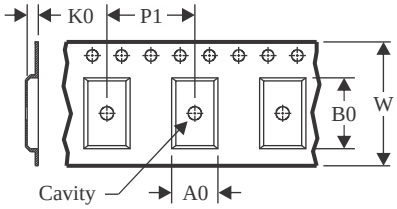
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

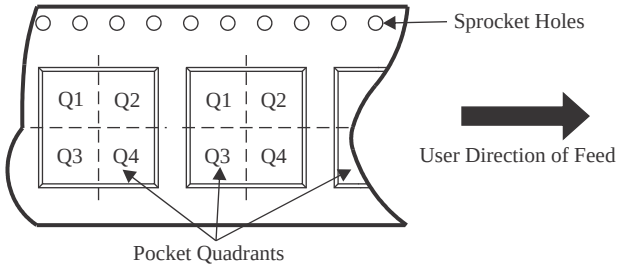


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

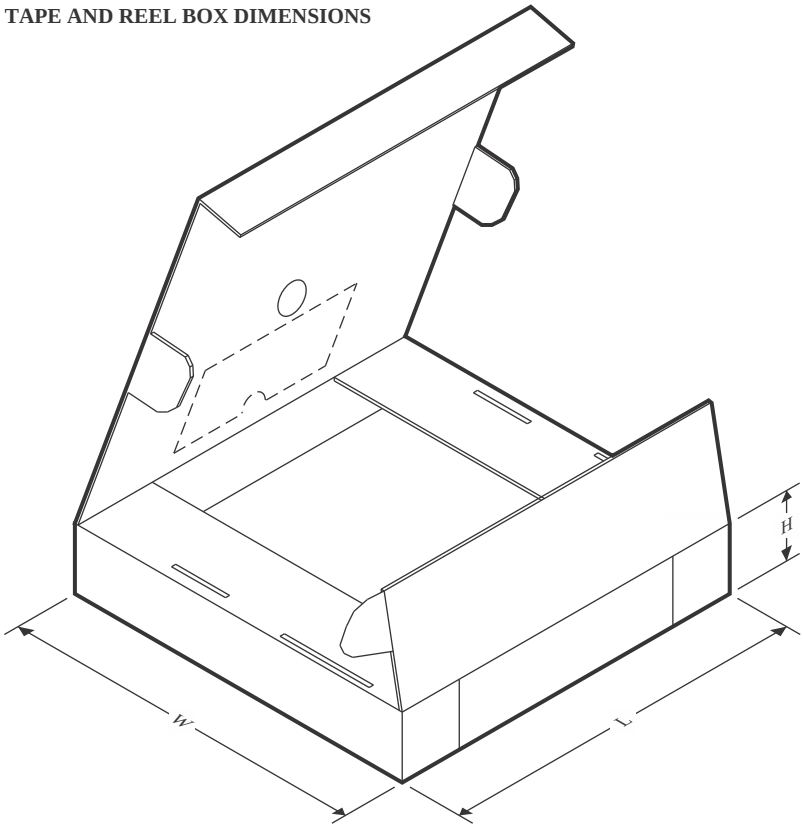
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3T3384DBQR	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CB3T3384DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74CB3T3384PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

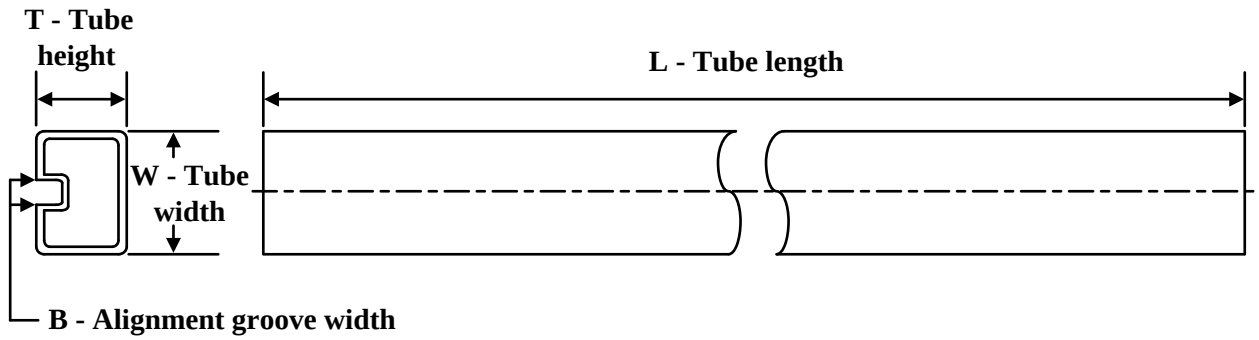
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3T3384DBQR	SSOP	DBQ	24	2500	356.0	356.0	35.0
SN74CB3T3384DWR	SOIC	DW	24	2000	350.0	350.0	43.0
SN74CB3T3384PWR	TSSOP	PW	24	2000	356.0	356.0	35.0

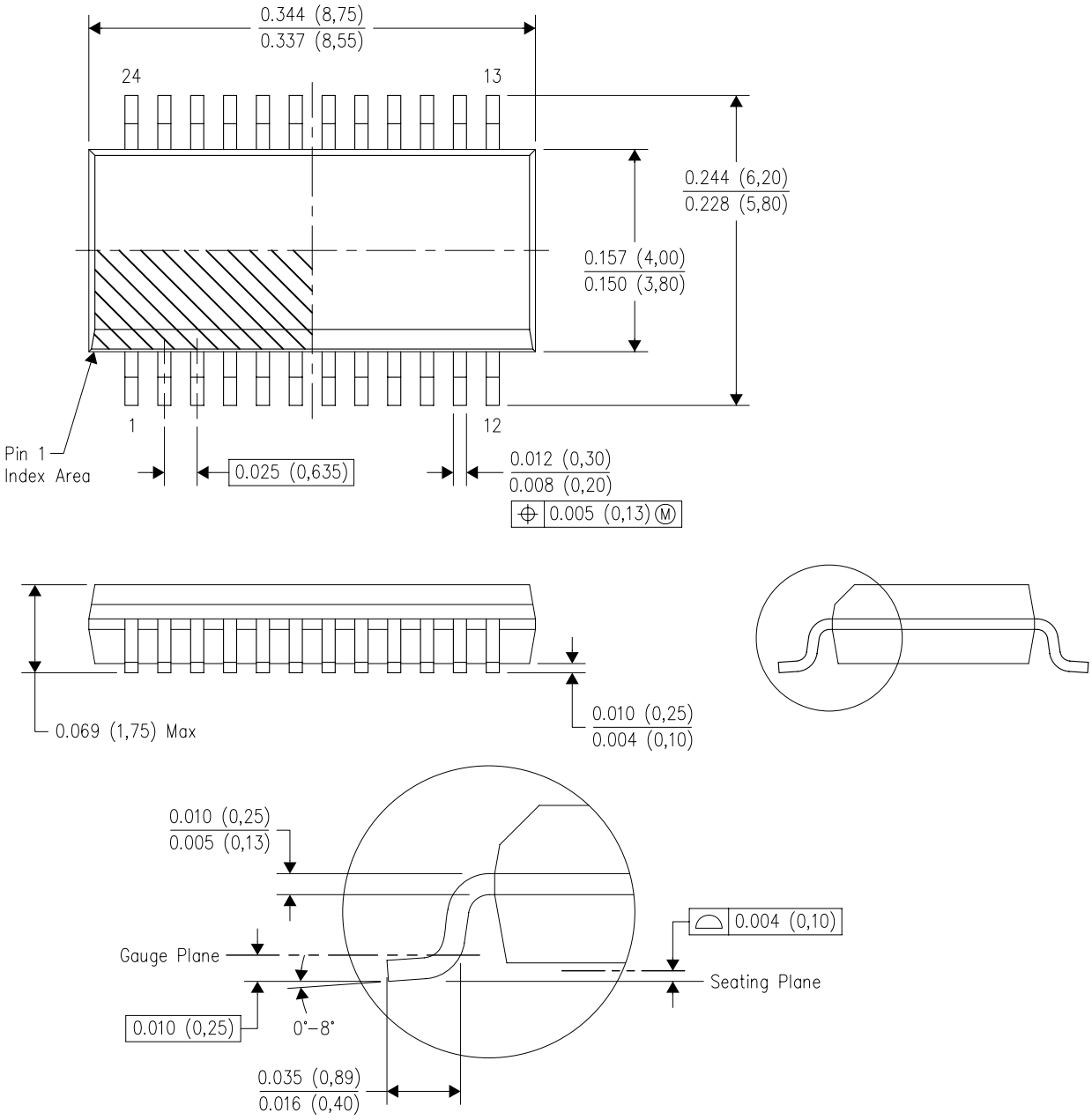
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74CB3T3384DW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74CB3T3384PW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74CB3T3384PWG4	PW	TSSOP	24	60	530	10.2	3600	3.5

DBQ (R–PDSO–G24) PLASTIC SMALL–OUTLINE PACKAGE



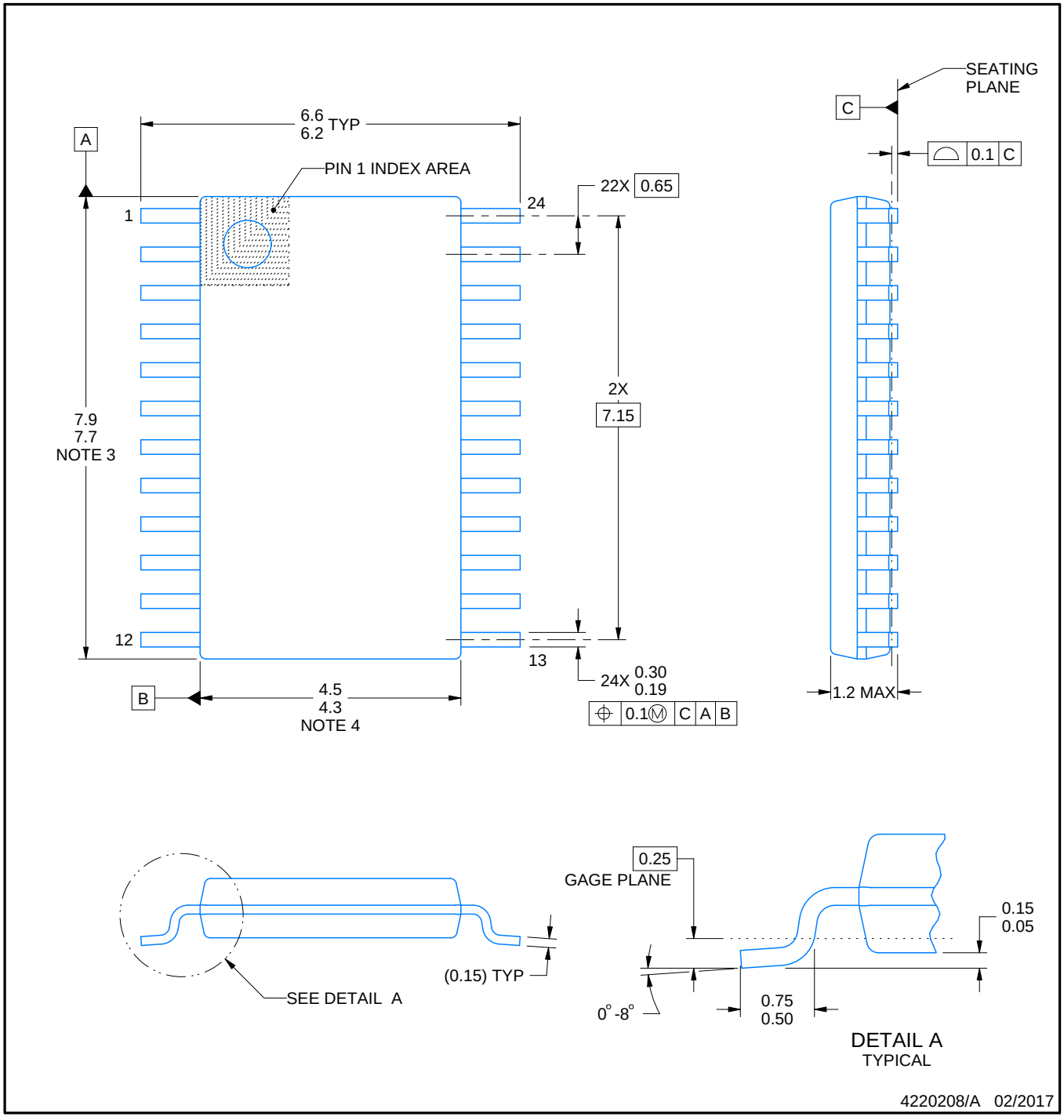
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
D. Falls within JEDEC MO–137 variation AE.

PACKAGE OUTLINE

PW0024A

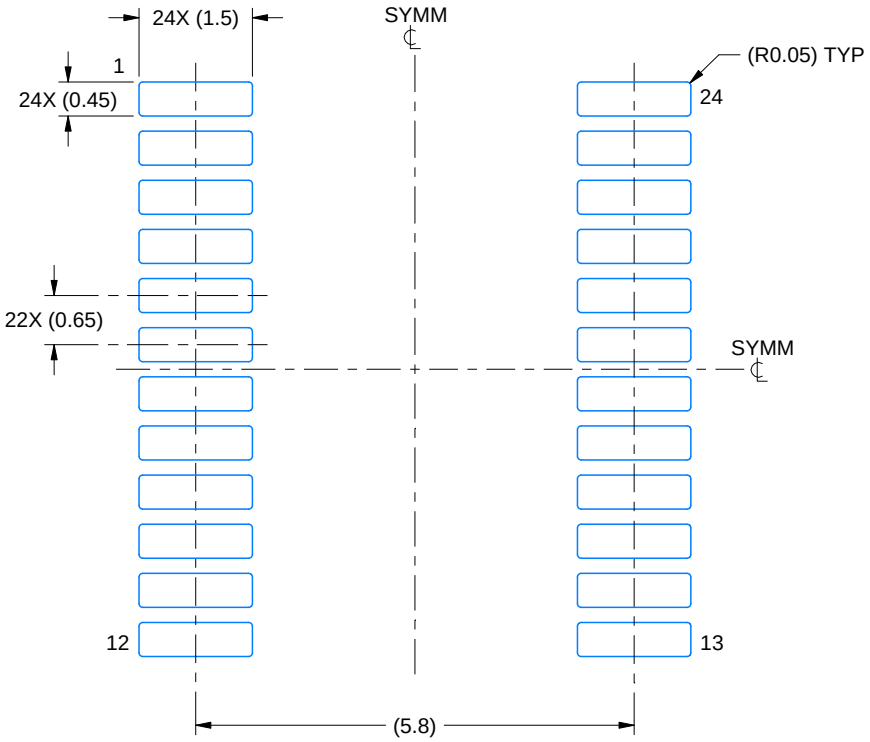
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

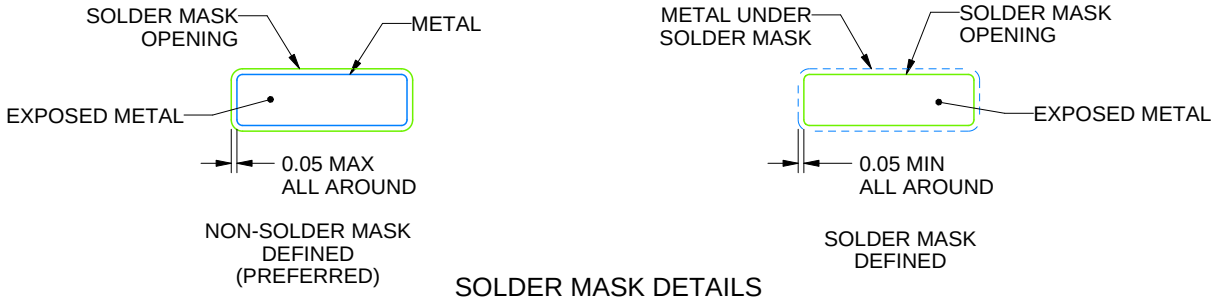


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

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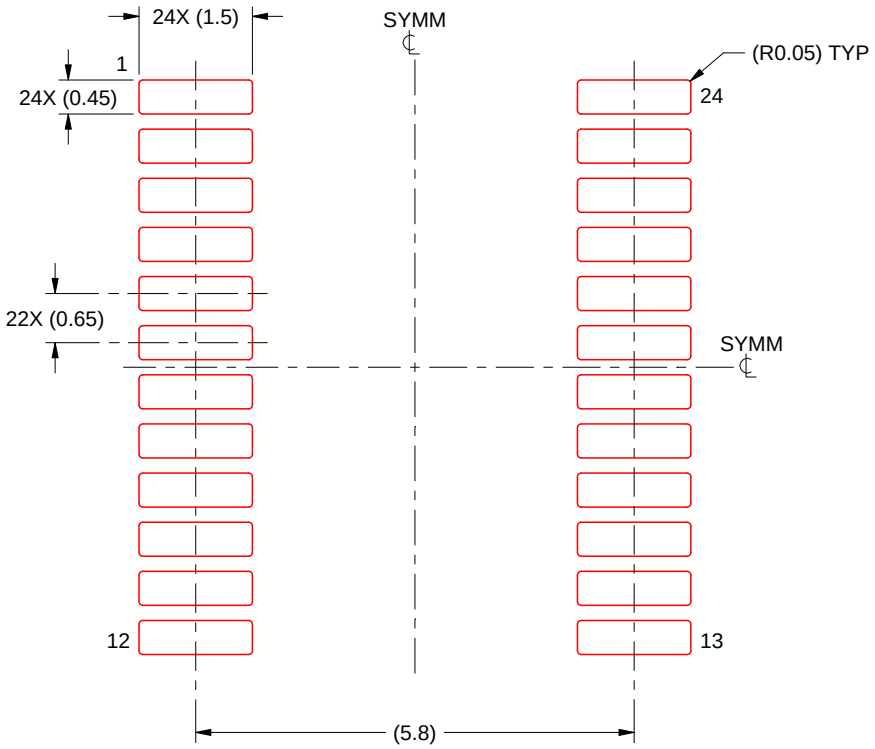
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



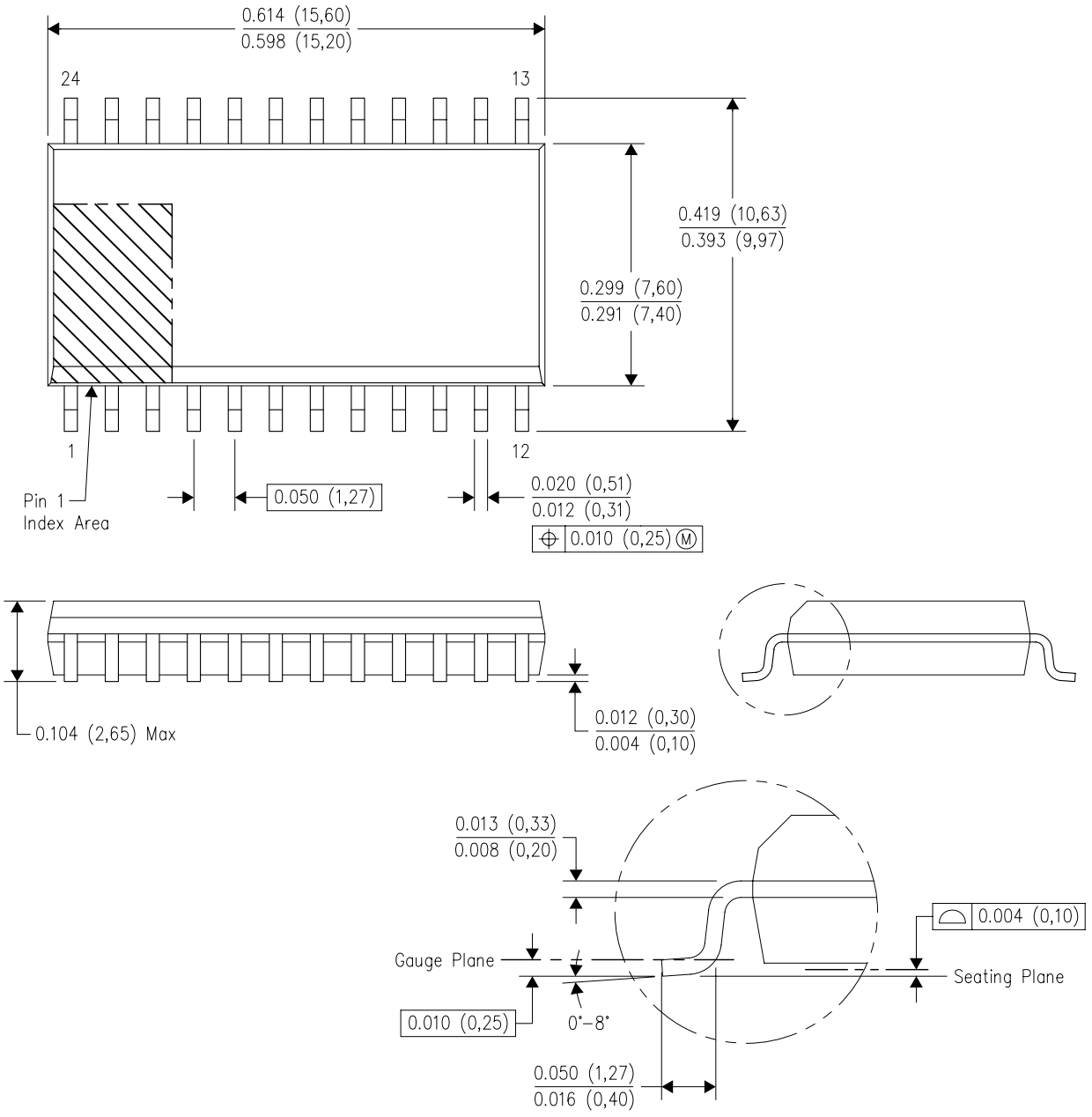
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220208/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AD.

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